SLOS094B – NOVEMBER 1970 – REVISED SEPTEMBER 2000

- Short-Circuit Protection
- Offset-Voltage Null Capability
- Large Common-Mode and Differential Voltage Ranges
- No Frequency Compensation Required
- Low Power Consumption
- No Latch-Up
- Designed to Be Interchangeable With Fairchild μA741

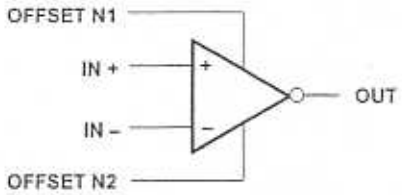
description

The μA741 is a general-purpose operational amplifier featuring offset-voltage null capability.

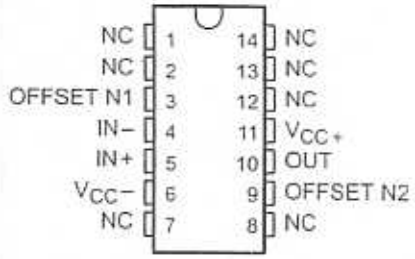
The high common-mode input voltage range and the absence of latch-up make the amplifier ideal for voltage-follower applications. The device is short-circuit protected and the internal frequency compensation ensures stability without external components. A low value potentiometer may be connected between the offset null inputs to null out the offset voltage as shown in Figure 2.

The μA741C is characterized for operation from 0°C to 70°C. The μA741I is characterized for operation from −40°C to 85°C.The μA741M is characterized for operation over the full military temperature range of −55°C to 125°C.

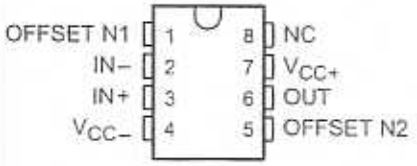
symbol



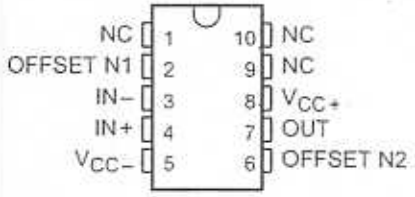
μA741M . . . J PACKAGE
(TOP VIEW)



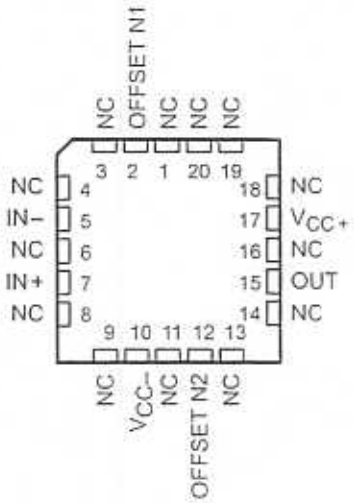
μA741M . . . JG PACKAGE
μA741C, μA741I . . . D, P, OR PW PACKAGE
(TOP VIEW)



μA741M . . . U PACKAGE
(TOP VIEW)



μA741M . . . FK PACKAGE
(TOP VIEW)



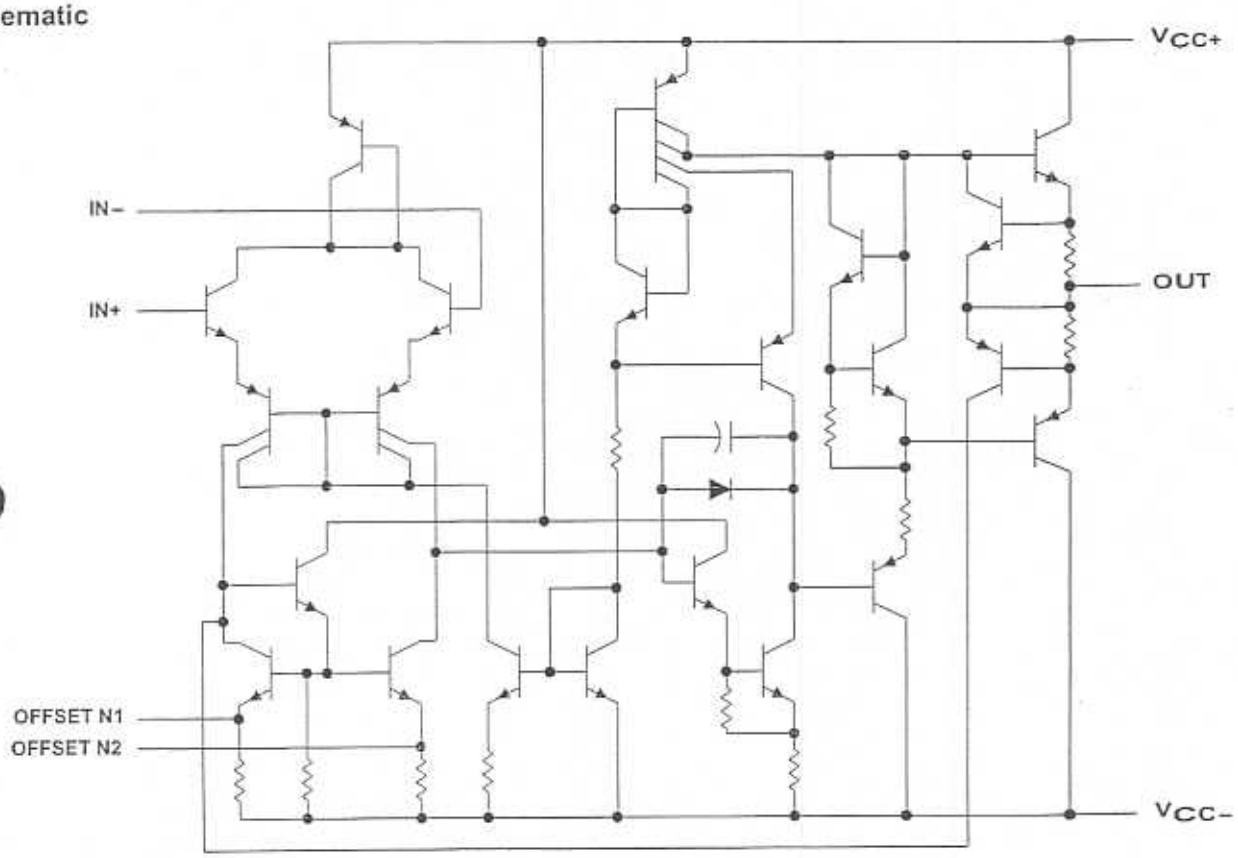
NC – No internal connection

AVAILABLE OPTIONS

T_A	PACKAGED DEVICES							CHIP FORM (Y)
	SMALL OUTLINE (D)	CHIP CARRIER (FK)	CERAMIC DIP (J)	CERAMIC DIP (JG)	PLASTIC DIP (P)	TSSOP (PW)	FLAT PACK (U)	
0°C to 70°C	μA741CD				μA741CP	μA741CPW		μA741Y
−40°C to 85°C	μA741ID				μA741IP			
−55°C to 125°C		μA741MFK	μA741MJ	μA741MJG			μA741MU	

The D package is available taped and reeled. Add the suffix R (e.g., μA741CDR).

schematic



Component Count	
Transistors	22
Resistors	11
Diode	1
Capacitor	1

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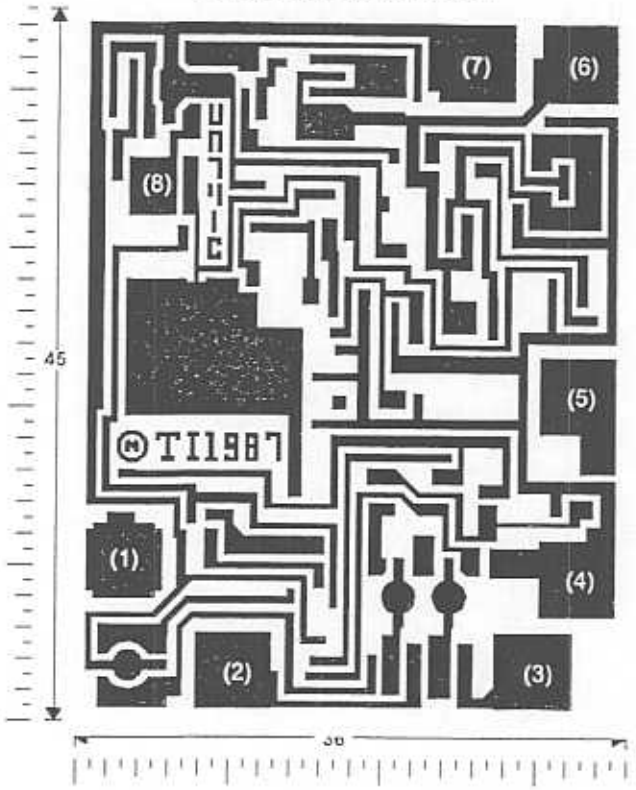
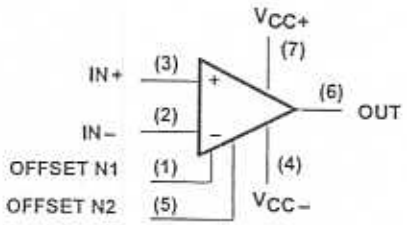
μA741Y chip information

This chip, when properly assembled, displays characteristics similar to the μA741C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.

BONDING PAD ASSIGNMENTS





CHIP THICKNESS: 15 TYPICAL

BONDING PADS: 4 × 4 MINIMUM

$T_{J}max$ = 150°C.

TOLERANCES ARE ±10%.

ALL DIMENSIONS ARE IN MILS.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

		μA741C	μA741I	μA741M	UNIT
Supply voltage, V_{CC+} (see Note 1)		18	22	22	V
Supply voltage, V_{CC-} (see Note 1)		−18	−22	−22	V
Differential input voltage, V_{ID} (see Note 2)		±15	±30	±30	V
Input voltage, V_I any input (see Notes 1 and 3)		±15	±15	±15	V
Voltage between offset null (either OFFSET N1 or OFFSET N2) and V_{CC-}		±15	±0.5	±0.5	V
Duration of output short circuit (see Note 4)		unlimited	unlimited	unlimited	
Continuous total power dissipation		See Dissipation Rating Table			
Operating free-air temperature range, T_A		0 to 70	−40 to 85	−55 to 125	°C
Storage temperature range		−65 to 150	−65 to 150	−65 to 150	°C
Case temperature for 60 seconds	FK package			260	°C
Lead temperature 1,6 mm (1/16 inch) from case for 60 seconds	J, JG, or U package			300	°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	D, P, or PW package	260	260		°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values, unless otherwise noted, are with respect to the midpoint between V_{CC+} and V_{CC-}.
2. Differential voltages are at IN+ with respect to IN−.
3. The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 V, whichever is less.
4. The output may be shorted to ground or either power supply. For the μA741M only, the unlimited duration of the short circuit applies at (or below) 125°C case temperature or 75°C free-air temperature.

DISSIPATION RATING TABLE

PACKAGE	$T_A \le 25°C$ POWER RATING	DERATING FACTOR	DERATE ABOVE T_A	$T_A = 70°C$ POWER RATING	$T_A = 85°C$ POWER RATING	$T_A = 125°C$ POWER RATING
D	500 mW	5.8 mW/°C	64°C	464 mW	377 mW	N/A
FK	500 mW	11.0 mW/°C	105°C	500 mW	500 mW	275 mW
J	500 mW	11.0 mW/°C	105°C	500 mW	500 mW	275 mW
JG	500 mW	8.4 mW/°C	90°C	500 mW	500 mW	210 mW
P	500 mW	N/A	N/A	500 mW	500 mW	N/A
PW	525 mW	4.2 mW/°C	25°C	336 mW	N/A	N/A
U	500 mW	5.4 mW/°C	57°C	432 mW	351 mW	135 mW

electrical characteristics at specified free-air temperature, $V_{CC\pm}$ = ±15 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	T_A†	μA741C			μA741I, μA741M			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
V_{IO}	Input offset voltage	V_O = 0	25°C		1	6		1	5	mV
			Full range			7.5			6	
$\Delta V_{IO(adj)}$	Offset voltage adjust range	V_O = 0	25°C		±15			±15		mV
I_{IO}	Input offset current	V_O = 0	25°C		20	200		20	200	nA
			Full range			300			500	
I_{IB}	Input bias current	V_O = 0	25°C		80	500		80	500	nA
			Full range			800			1500	
V_{ICR}	Common-mode input voltage range		25°C	±12	±13		±12	±13		V
			Full range	±12			±12			
V_{OM}	Maximum peak output voltage swing	R_L = 10 kΩ	25°C	±12	±14		±12	±14		V
		R_L ≥ 10 kΩ	Full range	±12			±12			
		R_L = 2 kΩ	25°C	±10	±13		±10	±13		
		R_L ≥ 2 kΩ	Full range	±10			±10			
A_{VD}	Large-signal differential voltage amplification	R_L ≥ 2 kΩ	25°C	20	200		50	200		V/mV
		V_O = ±10 V	Full range	15			25			
r_i	Input resistance		25°C	0.3	2		0.3	2		MΩ
r_o	Output resistance	V_O = 0, See Note 5	25°C		75			75		Ω
C_i	Input capacitance		25°C		1.4			1.4		pF
CMRR	Common-mode rejection ratio	V_{IC} = V_{ICR}min	25°C	70	90		70	90		dB
			Full range	70			70			
k_{SVS}	Supply voltage sensitivity ($\Delta V_{IO}/\Delta V_{CC}$)	V_{CC} = ±9 V to ±15 V	25°C		30	150		30	150	μV/V
			Full range			150			150	
I_{OS}	Short-circuit output current		25°C		±25	±40		±25	±40	mA
I_{CC}	Supply current	V_O = 0, No load	25°C		1.7	2.8		1.7	2.8	mA
			Full range			3.3			3.3	
P_D	Total power dissipation	V_O = 0, No load	25°C		50	85		50	85	mW
			Full range			100			100	

† All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise specified. Full range for the μA741C is 0°C to 70°C, the μA741I is –40°C to 85°C, and the μA741M is –55°C to 125°C.

NOTE 5: This typical value applies only at frequencies above a few hundred hertz because of the effects of drift and thermal feedback.

operating characteristics, $V_{CC\pm}$ = ±15 V, T_A = 25°C

PARAMETER		TEST CONDITIONS		μA741C			μA741I, μA741M			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
t_r	Rise time	V_I = 20 mV, C_L = 100 pF,	R_L = 2 kΩ, See Figure 1		0.3			0.3		μs
	Overshoot factor				5%			5%		
SR	Slew rate at unity gain	V_I = 10 V, C_L = 100 pF,	R_L = 2 kΩ, See Figure 1		0.5			0.5		V/μs

Electrical characteristics at specified free-air temperature, $V_{CC\pm}$ = ±15 V, T_A = 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	μA741Y			UNIT
			MIN	TYP	MAX	
V_{IO}	Input offset voltage	V_O = 0		1	6	mV
$\Delta V_{IO(adj)}$	Offset voltage adjust range	V_O = 0		±15		mV
I_{IO}	Input offset current	V_O = 0		20	200	nA
I_{IB}	Input bias current	V_O = 0		80	500	nA
V_{ICR}	Common-mode input voltage range		±12	±13		V
V_{OM}	Maximum peak output voltage swing	R_L = 10 kΩ	±12	±14		V
		R_L = 2 kΩ	±10	±13		
A_{VD}	Large-signal differential voltage amplification	$R_L \geq$ 2 kΩ	20	200		V/mV
r_i	Input resistance		0.3	2		MΩ
r_o	Output resistance	V_O = 0, See Note 5		75		Ω
C_i	Input capacitance			1.4		pF
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR}$min	70	90		dB
k_{SVS}	Supply voltage sensitivity ($\Delta V_{IO}/\Delta V_{CC}$)	V_{CC} = ±9 V to ±15 V		30	150	μV/V
I_{OS}	Short-circuit output current			±25	±40	mA
I_{CC}	Supply current	V_O = 0, No load		1.7	2.8	mA
P_D	Total power dissipation	V_O = 0, No load		50	85	mW

† All characteristics are measured under open-loop conditions with zero common-mode voltage unless otherwise specified.
NOTE 5: This typical value applies only at frequencies above a few hundred hertz because of the effects of drift and thermal feedback.

Operating characteristics, $V_{CC\pm}$ = ±15 V, T_A = 25°C

PARAMETER		TEST CONDITIONS	μA741Y			UNIT
			MIN	TYP	MAX	
t_r	Rise time	V_I = 20 mV, R_L = 2 kΩ, C_L = 100 pF, See Figure 1		0.3		μs
	Overshoot factor			5%		
SR	Slew rate at unity gain	V_I = 10 V, R_L = 2 kΩ, C_L = 100 pF, See Figure 1		0.5		V/μs

PARAMETER MEASUREMENT INFORMATION

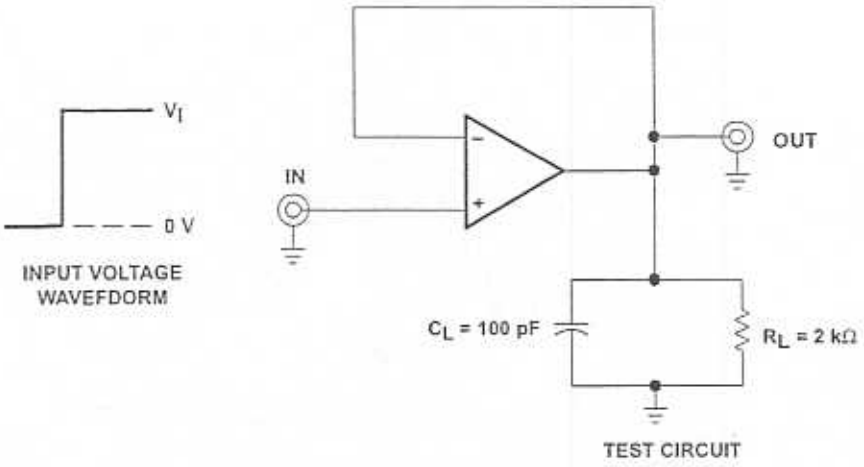


Figure 1. Rise Time, Overshoot, and Slew Rate

APPLICATION INFORMATION

Figure 2 shows a diagram for an input offset voltage null circuit.

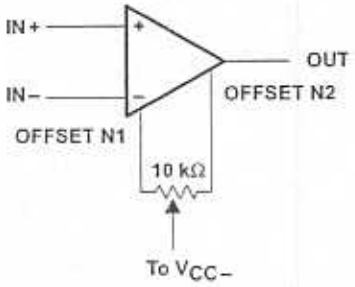


Figure 2. Input Offset Voltage Null Circuit

TYPICAL CHARACTERISTICS†

INPUT OFFSET CURRENT
vs
FREE-AIR TEMPERATURE

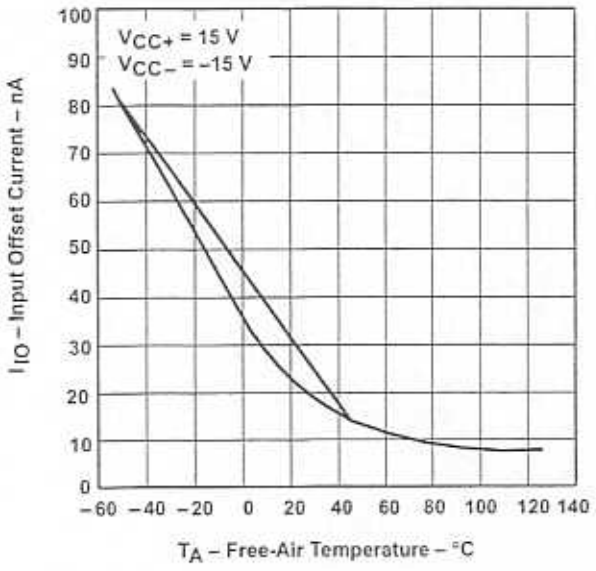


Figure 3

INPUT BIAS CURRENT
vs
FREE-AIR TEMPERATURE

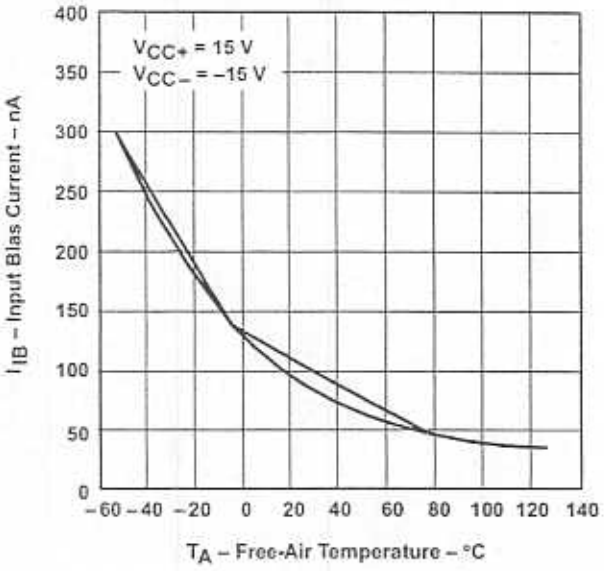


Figure 4

MAXIMUM PEAK OUTPUT VOLTAGE
vs
LOAD RESISTANCE

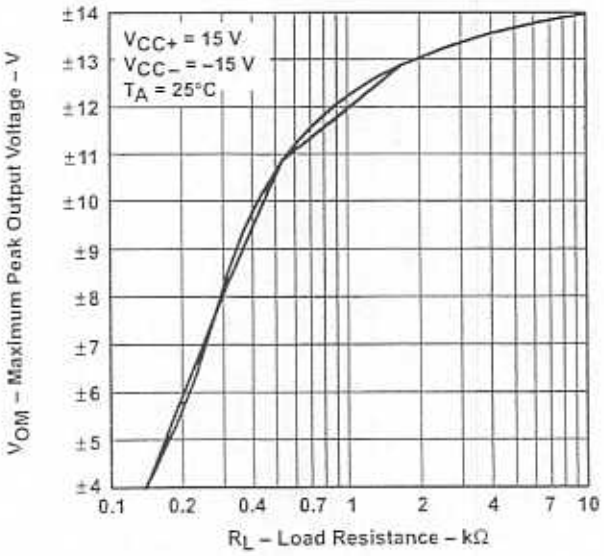


Figure 5

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

TYPICAL CHARACTERISTICS

MAXIMUM PEAK OUTPUT VOLTAGE
vs
FREQUENCY

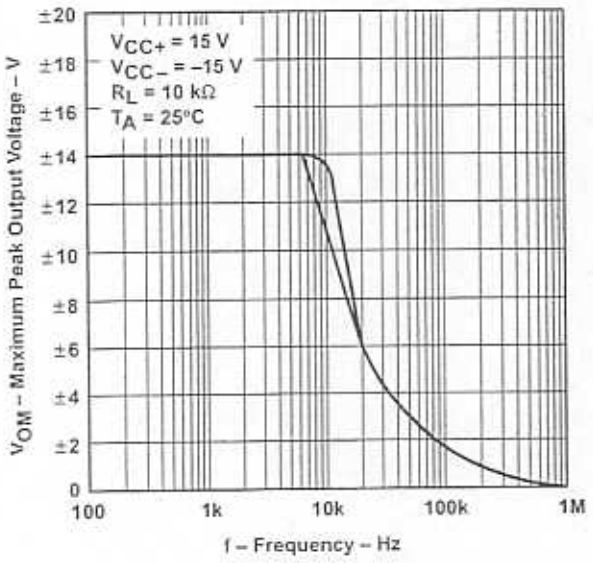


Figure 6

OPEN-LOOP SIGNAL DIFFERENTIAL
VOLTAGE AMPLIFICATION
vs
SUPPLY VOLTAGE

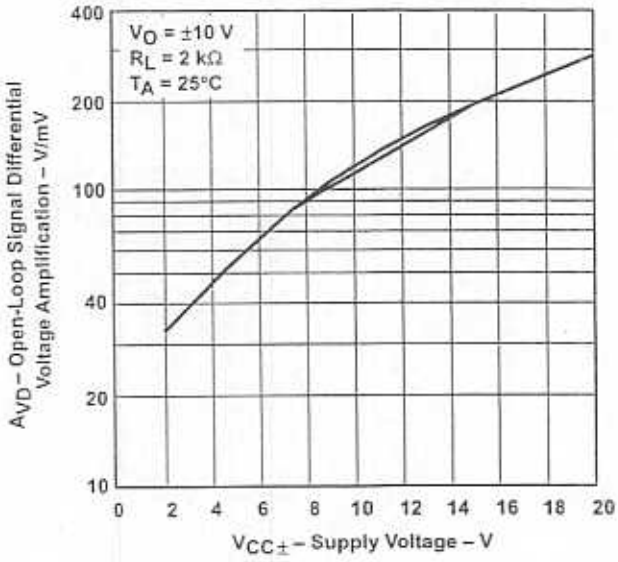
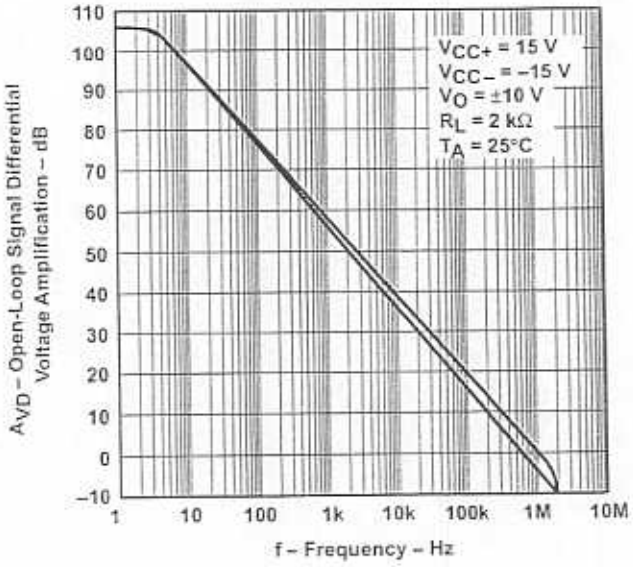


Figure 7

OPEN-LOOP LARGE-SIGNAL DIFFERENTIAL
VOLTAGE AMPLIFICATION
vs
FREQUENCY



TYPICAL CHARACTERISTICS

COMMON-MODE REJECTION RATIO
vs
FREQUENCY

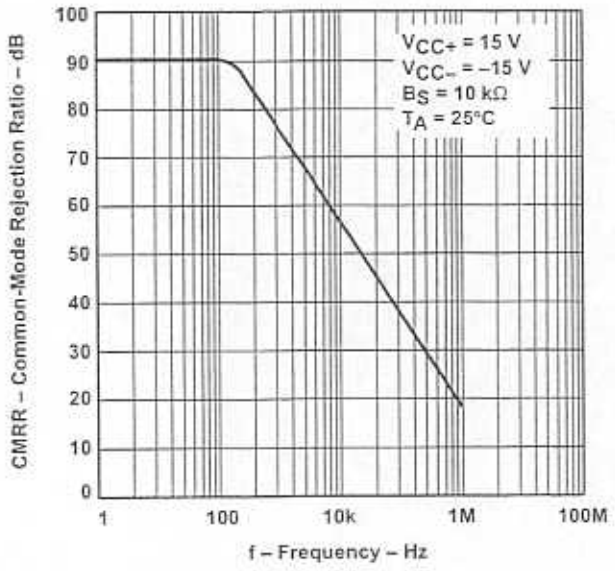


Figure 8

OUTPUT VOLTAGE
vs
ELAPSED TIME

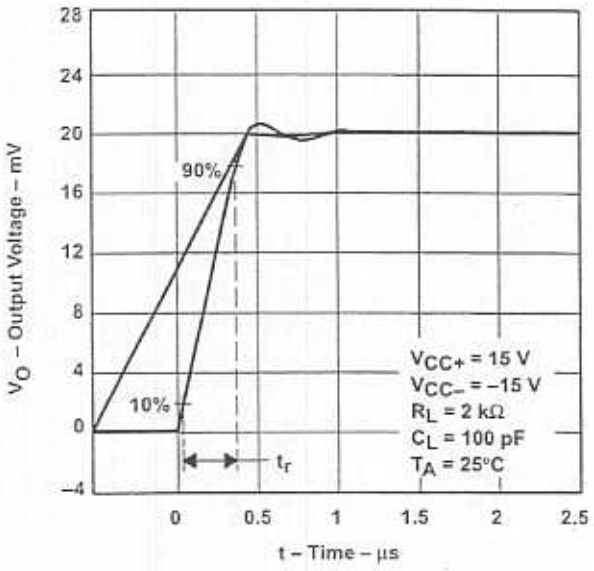


Figure 9

VOLTAGE-FOLLOWER
LARGE-SIGNAL PULSE RESPONSE

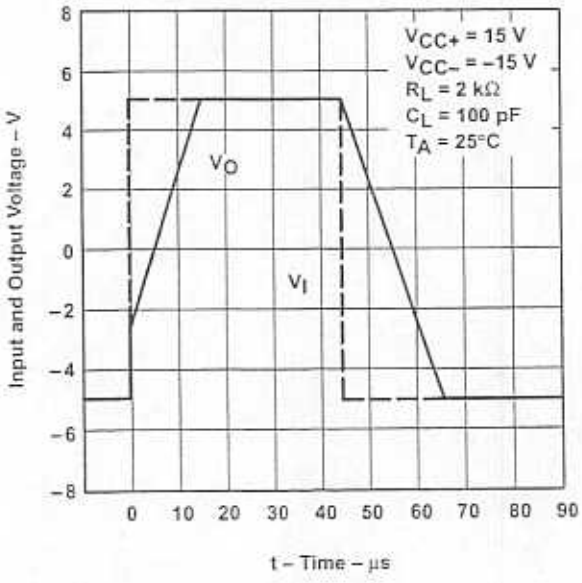


Figure 10

National Semiconductor

December 2001

LF155/LF156/LF256/LF257/LF355/LF356/LF357 JFET Input Operational Amplifiers

General Description

These are the first monolithic JFET input operational amplifiers to incorporate well matched, high voltage JFETs on the same chip with standard bipolar transistors (BI-FET™ Technology). These amplifiers feature low input bias and offset currents/low offset voltage and offset voltage drift, coupled with offset adjust which does not degrade drift or common-mode rejection. The devices are also designed for high slew rate, wide bandwidth, extremely fast settling time, low voltage and current noise and a low 1/f noise corner.

Features

Advantages

- Replace expensive hybrid and module FET op amps
- Rugged JFETs allow blow-out free handling compared with MOSFET input devices
- Excellent for low noise applications using either high or low source impedance — very low 1/f corner
- Offset adjust does not degrade drift or common-mode rejection as in most monolithic amplifiers
- New output stage allows use of large capacitive loads (5,000 pF) without stability problems
- Internal compensation and large differential input voltage capability

Applications

- Precision high speed integrators
- Fast D/A and A/D converters
- High impedance buffers
- Wideband, low noise, low drift amplifiers
- Logarithmic amplifiers
- Photocell amplifiers
- Sample and Hold circuits

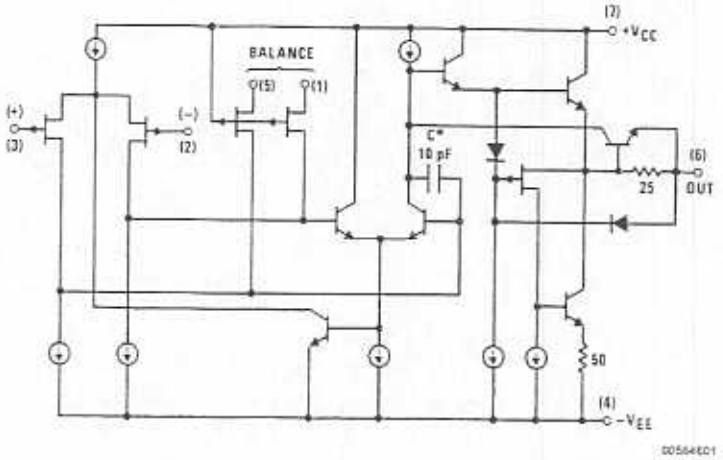
Common Features

- Low input bias current: 30pA
- Low Input Offset Current: 3pA
- High input impedance: $10^{12}\Omega$
- Low input noise current: $0.01\ pA/\sqrt{Hz}$
- High common-mode rejection ratio: 100 dB
- Large dc voltage gain: 106 dB

Uncommon Features

	LF155/ LF355	LF156/ LF256/ LF356	LF257/ LF357 (A_V=5)	Units
■ Extremely fast settling time to 0.01%	4	1.5	1.5	µs
■ Fast slew rate	5	12	50	V/µs
■ Wide gain bandwidth	2.5	5	20	MHz
■ Low input noise voltage	20	12	12	$nV/\sqrt{Hz}$

Simplified Schematic



*3pF in LF357 series

BI-FET™, BI-FET II™ are trademarks of National Semiconductor Corporation

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, contact the National Semiconductor Sales Office/Distributors for availability and specifications.

	LF155/6	LF256/7/LF356B	LF355/6/7
Supply Voltage	±22V	±22V	±18V
Differential Input Voltage	±40V	±40V	±30V
Input Voltage Range (Note 2)	±20V	±20V	±16V
Output Short Circuit Duration	Continuous	Continuous	Continuous
T_{JMAX}			
H-Package	150°C	115°C	115°C
N-Package		100°C	100°C
M-Package		100°C	100°C
Power Dissipation at T_A = 25°C (Notes 1, 8)			
H-Package (Still Air)	560 mW	400 mW	400 mW
H-Package (400 LF/Min Air Flow)	1200 mW	1000 mW	1000 mW
N-Package		670 mW	670 mW
M-Package		380 mW	380 mW
Thermal Resistance (Typical) θ_{JA}			
H-Package (Still Air)	160°C/W	160°C/W	160°C/W
H-Package (400 LF/Min Air Flow)	65°C/W	65°C/W	65°C/W
N-Package		130°C/W	130°C/W
M-Package		195°C/W	195°C/W
(Typical) θ_{JC}			
H-Package	23°C/W	23°C/W	23°C/W
Storage Temperature Range	−65°C to +150°C	−65°C to +150°C	−65°C to +150°C
Soldering Information (Lead Temp.)			
Metal Can Package			
Soldering (10 sec.)	300°C	300°C	300°C
Dual-In-Line Package			
Soldering (10 sec.)	260°C	260°C	260°C
Small Outline Package			
Vapor Phase (60 sec.)		215°C	215°C
Infrared (15 sec.)		220°C	220°C
See AN-450 "Surface Mounting Methods and Their Effect on Product Reliability" for other methods of soldering surface mount devices.			
ESD tolerance			
(100 pF discharged through 1.5kΩ)	1000V	1000V	1000V

DC Electrical Characteristics

(Note 3)

Symbol	Parameter	Conditions	LF155/6			LF256/7 LF356B			LF355/6/7			Units
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
V_{OS}	Input Offset Voltage	R_S=50Ω, T_A=25°C		3	5		3	5		3	10	mV
		Over Temperature			7			6.5			13	mV
$\Delta V_{OS}/\Delta T$	Average TC of Input Offset Voltage	R_S=50Ω		5			5			5		µV/°C
$\Delta TC/\Delta V_{OS}$	Change in Average TC with V_{OS} Adjust	R_S=50Ω, (Note 4)		0.5			0.5			0.5		µV/°C per mV
I_{OS}	Input Offset Current	T_J=25°C, (Notes 3, 5)		3	20		3	20		3	50	pA
		$T_J \leq T_{HIGH}$			20			1			2	nA

DC Electrical Characteristics (Continued)

(Note 3)

Symbol	Parameter	Conditions	LF155/6			LF256/7 LF356B			LF355/6/7			Units
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_B	Input Bias Current	T_J=25°C, (Notes 3, 5)		30	100		30	100		30	200	pA
		$T_J \leq T_{HIGH}$			50			5			8	nA
R_{IN}	Input Resistance	T_J=25°C		10^{12}			10^{12}			10^{12}		Ω
A_{VOL}	Large Signal Voltage Gain	V_S=±15V, T_A=25°C	50	200		50	200		25	200		V/mV
		V_O=±10V, R_L=2k										
		Over Temperature	25			25			15			V/mV
V_O	Output Voltage Swing	V_S=±15V, R_L=10k	±12	±13		±12	±13		±12	±13		V
		V_S=±15V, R_L=2k	±10	±12		±10	±12		±10	±12		V
V_{CM}	Input Common-Mode Voltage Range	V_S=±15V	±11	+15.1 −12		±11	±15.1 −12		+10	+15.1 −12		V V
CMRR	Common-Mode Rejection Ratio		85	100		85	100		80	100		dB
PSRR	Supply Voltage Rejection Ratio	(Note 6)	85	100		85	100		80	100		dB

DC Electrical Characteristics

$T_A = T_J = 25°C$, $V_S = ±15V$

Parameter	LF155		LF355		LF156/256/257/356B		LF356		LF357		Units
	Typ	Max	Typ	Max	Typ	Max	Typ	Max	Typ	Max	
Supply Current	2	4	2	4	5	7	5	10	5	10	mA

AC Electrical Characteristics

$T_A = T_J = 25°C$, $V_S = ±15V$

Symbol	Parameter	Conditions	LF155/355	LF156/256/356B	LF156/256/356/LF356B	LF257/357	Units
			Typ	Min	Typ	Typ	
SR	Slew Rate	LF155/6: A_V=1,	5	7.5	12		V/µs
		LF357: A_V=5				50	V/µs
GBW	Gain Bandwidth Product		2.5		5	20	MHz
t_s	Settling Time to 0.01%	(Note 7)	4		1.5	1.5	µs
e_n	Equivalent Input Noise Voltage	R_S=100Ω					
		f=100 Hz	25		15	15	$nV/\sqrt{Hz}$
		f=1000 Hz	20		12	12	$nV/\sqrt{Hz}$
i_n	Equivalent Input Current Noise	f=100 Hz	0.01		0.01	0.01	$pA/\sqrt{Hz}$
		f=1000 Hz	0.01		0.01	0.01	$pA/\sqrt{Hz}$
C_{IN}	Input Capacitance		3		3	3	pF

Notes for Electrical Characteristics

Note 1: The maximum power dissipation for these devices must be derated at elevated temperatures and is dictated by T_{JMAX}, θ_{JA}, and the ambient temperature, T_A. The maximum available power dissipation at any temperature is $P_D=(T_{JMAX}-T_A)/\theta_{JA}$ or the 25°C P_{DMAX}, whichever is less.

Note 2: Unless otherwise specified the absolute maximum negative input voltage is equal to the negative power supply voltage.

Note 3: Unless otherwise stated, these test conditions apply:

Notes for Electrical Characteristics (Continued)

	LF155/156	LF256/257	LF356B	LF355/6/7
Supply Voltage, V_S	$\pm 15V \le V_S \le \pm 20V$	$\pm 15V \le V_S \le \pm 20V$	$\pm 15V \le V_S \pm 20V$	$V_S = \pm 15V$
T_A	$-55°C \le T_A \le +125°C$	$-25°C \le T_A \le +85°C$	$0°C \le T_A \le +70°C$	$0°C \le T_A \le +70°C$
T_{HIGH}	+125°C	+85°C	+70°C	+70°C

and V_{OS}. I_B and I_{OS} are measured at $V_{CM} = 0$.

Note 4: The Temperature Coefficient of the adjusted input offset voltage changes only a small amount (0.5μV/°C typically) for each mV of adjustment from its original unadjusted value. Common-mode rejection and open loop voltage gain are also unaffected by offset adjustment.

Note 5: The input bias currents are junction leakage currents which approximately double for every 10°C increase in the junction temperature, T_J. Due to limited production test time, the input bias currents measured are correlated to junction temperature. In normal operation the junction temperature rises above the ambient temperature as a result of internal power dissipation, Pd. $T_J = T_A + \theta_{JA}$ Pd where θ_{JA} is the thermal resistance from junction to ambient. Use of a heat sink is recommended if input bias current is to be kept to a minimum.

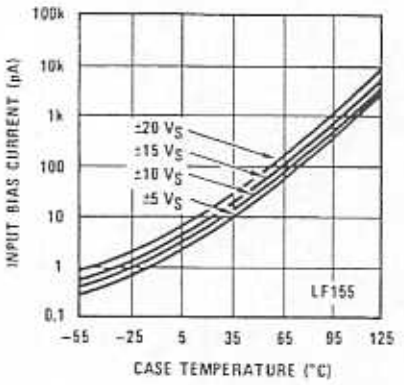
Note 6: Supply Voltage Rejection is measured for both supply magnitudes increasing or decreasing simultaneously, in accordance with common practice.

Note 7: Settling time is defined here, for a unity gain inverter connection using 2 kΩ resistors for the LF155/6. It is the time required for the error voltage (the voltage at the inverting input pin on the amplifier) to settle to within 0.01% of its final value from the time a 10V step input is applied to the inverter. For the LF357, $A_V = -5$, the feedback resistor from output to input is 2kΩ and the output step is 10V (See Settling Time Test Circuit).

Note 8: Max. Power Dissipation is defined by the package characteristics. Operating the part near the Max. Power Dissipation may cause the part to operate outside guaranteed limits.

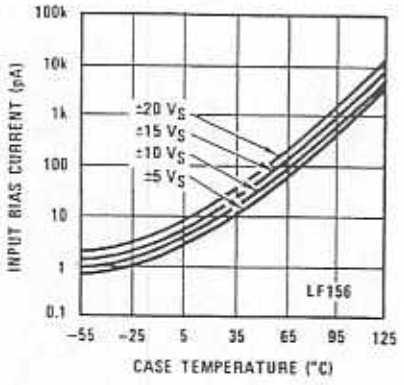
Typical DC Performance Characteristics Curves are for LF155 and LF156 unless otherwise specified.

Input Bias Current



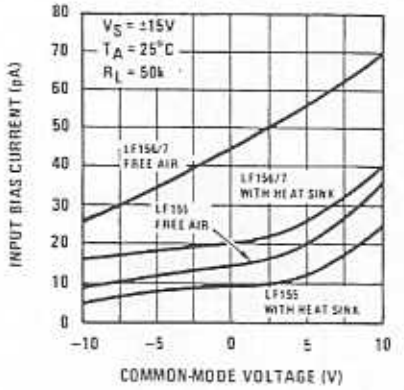
00564637

Input Bias Current



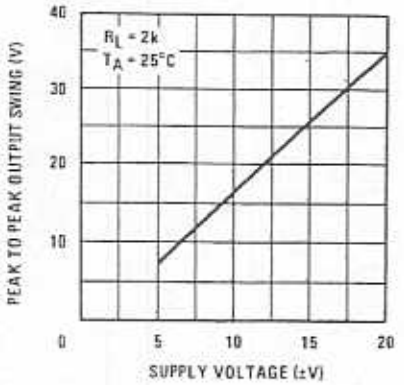
00564638

Input Bias Current



00564639

Voltage Swing

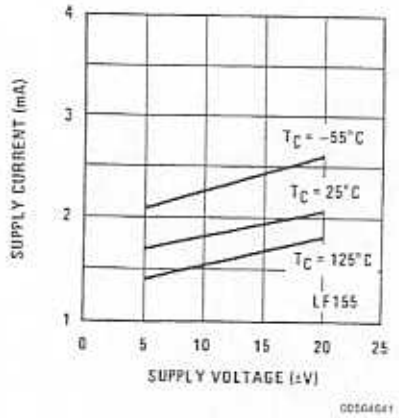


00564640

Typical DC Performance Characteristics

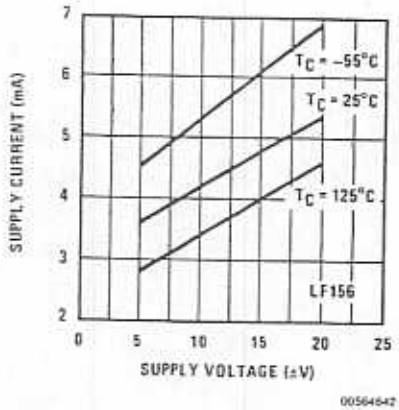
Curves are for LF155 and LF156 unless otherwise specified. (Continued)

Supply Current



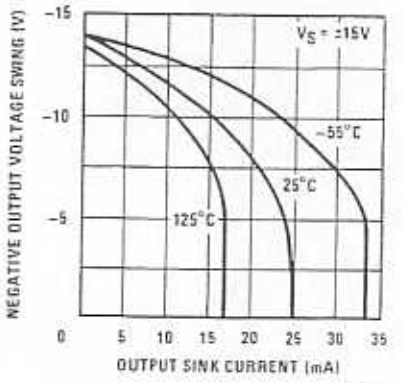
00564641

Supply Current



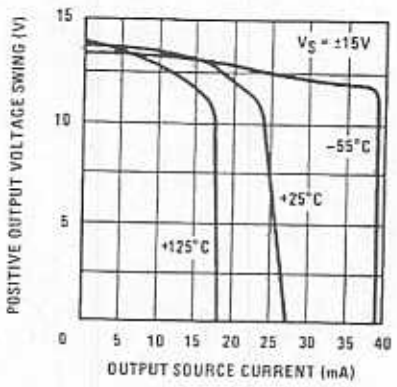
00564642

Negative Current Limit



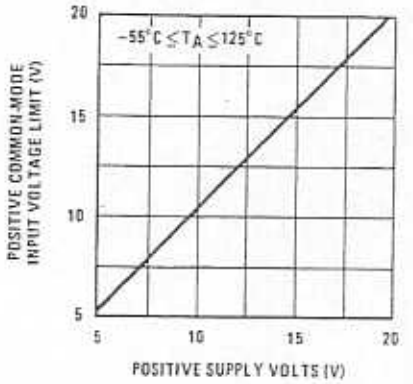
00564643

Positive Current Limit



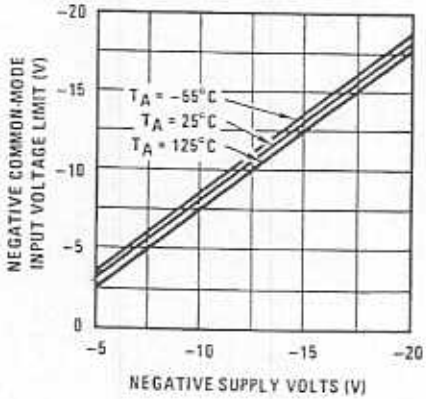
00564644

Positive Common-Mode Input Voltage Limit



00564645

Negative Common-Mode Input Voltage Limit

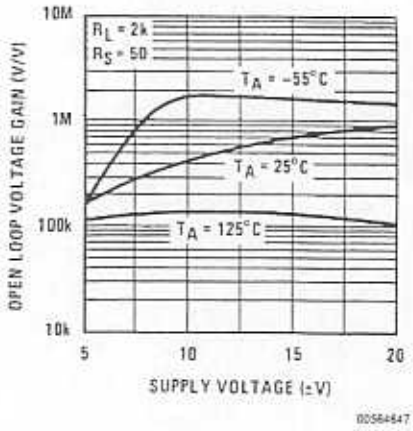


00564646

Typical DC Performance Characteristics

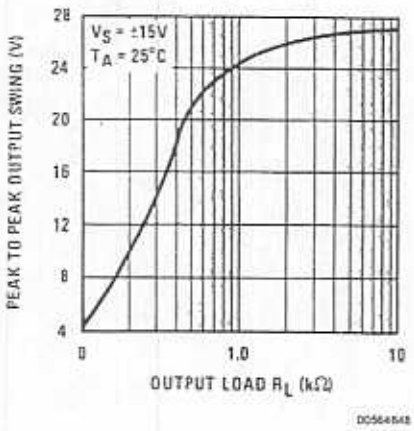
Curves are for LF155 and LF156 unless otherwise specified. (Continued)

Open Loop Voltage Gain



00564647

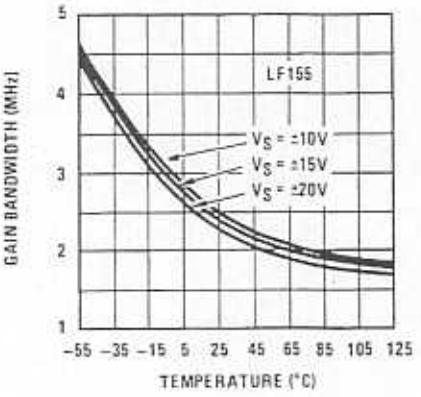
Output Voltage Swing



00564648

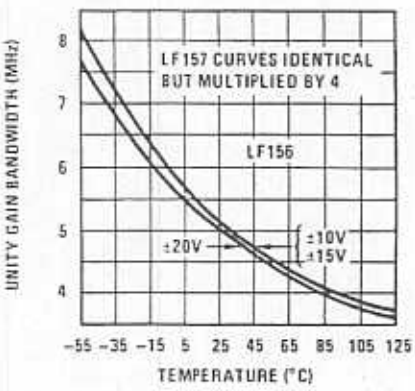
Typical AC Performance Characteristics

Gain Bandwidth



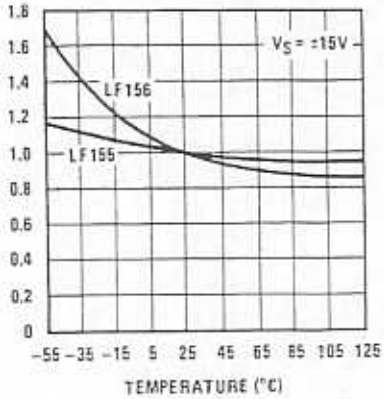
00564649

Gain Bandwidth



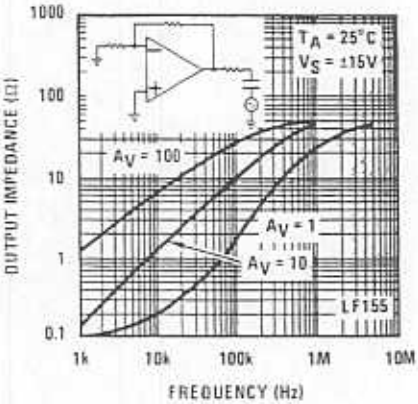
00564650

Normalized Slew Rate



00564651

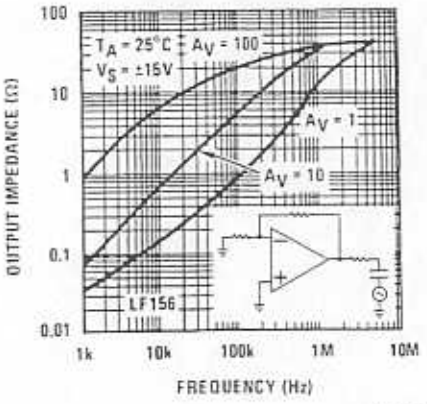
Output Impedance



00564652

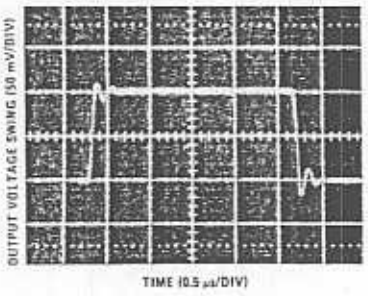
Typical AC Performance Characteristics (Continued)

Output Impedance



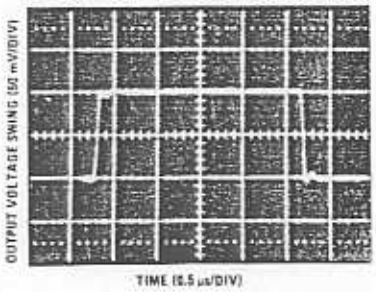
00564653

LF155 Small Signal Pulse Response, A_V = +1



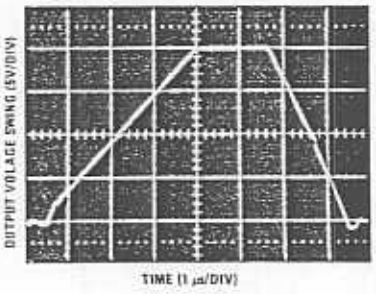
00564605

LF156 Small Signal Pulse Response, A_V = +1



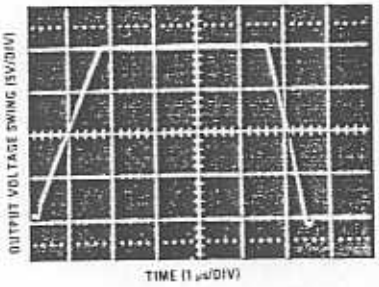
00564606

LF155 Large Signal Pulse Response, A_V = +1



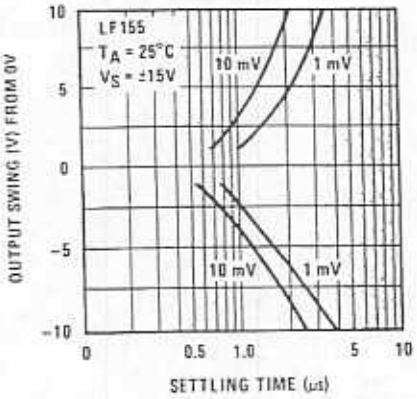
00564608

LF156 Large Signal Puls Response, A_V = +1



00564607

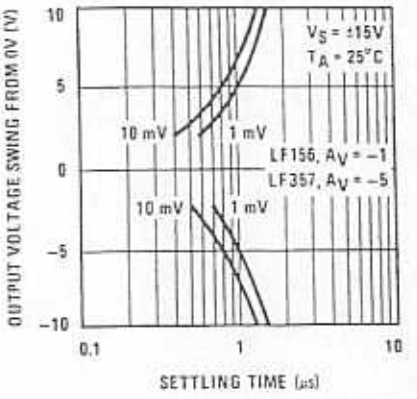
Inverter Settling Time



00564655

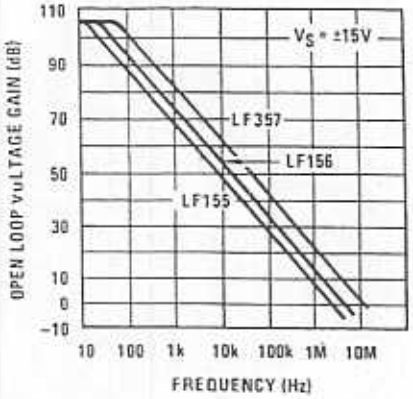
Typical AC Performance Characteristics (Continued)

Inverter Settling Time



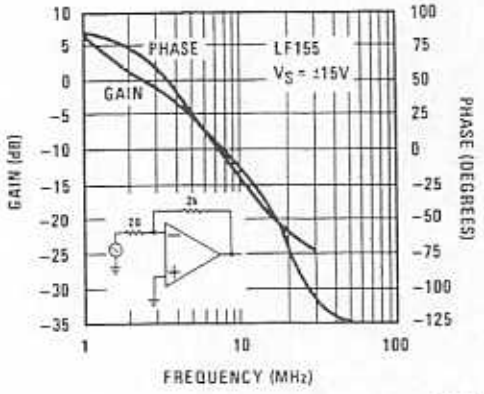
00564656

Open Loop Frequency Response



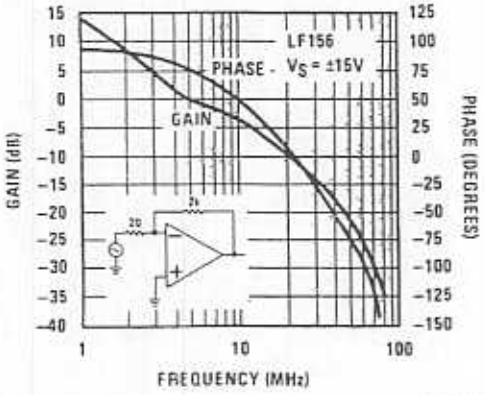
00564657

Bode Plot



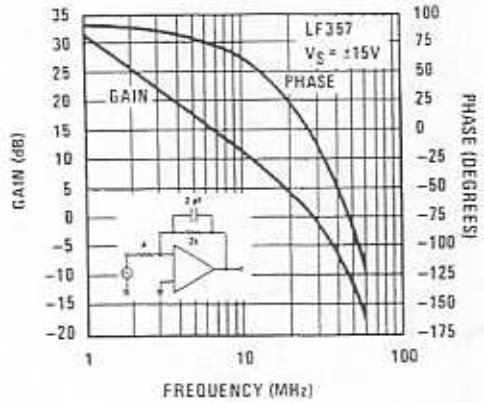
00564658

Bode Plot



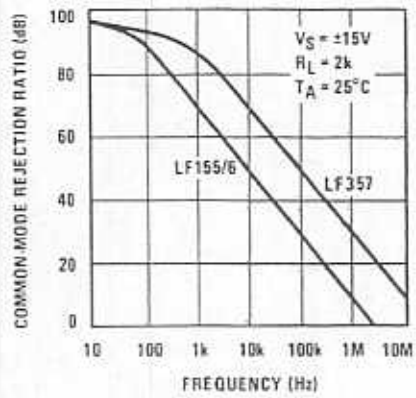
00564659

Bode Plot



00564660

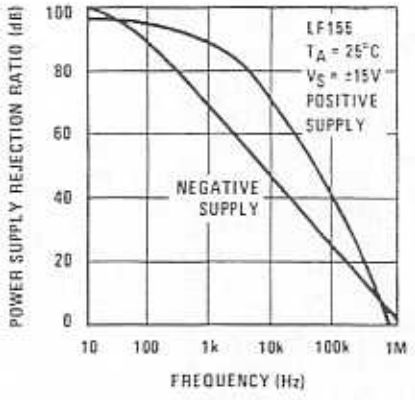
Common-Mode Rejection Ratio



00564661

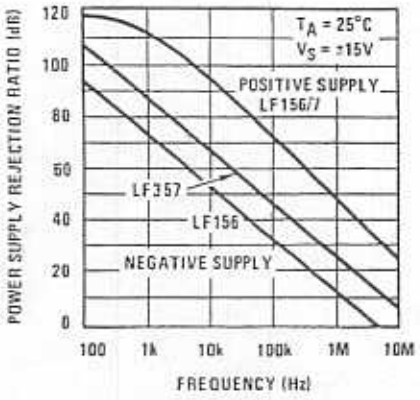
Typical AC Performance Characteristics (Continued)

Power Supply Rejection Ratio



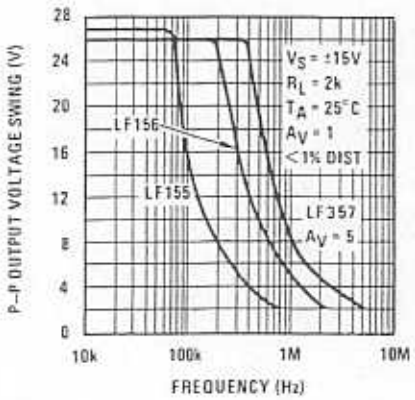
00564662

Power Supply Rejection Ratio



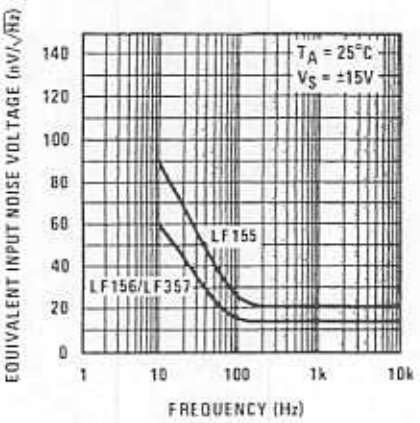
00564663

Undistorted Output Voltage Swing



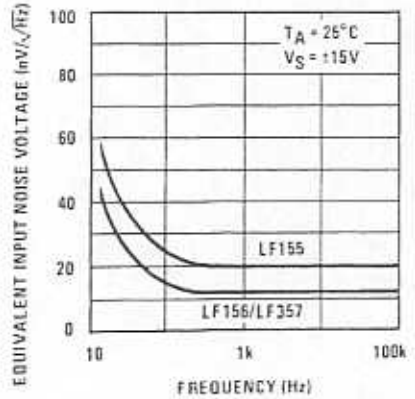
00564664

Equivalent Input Noise Voltage



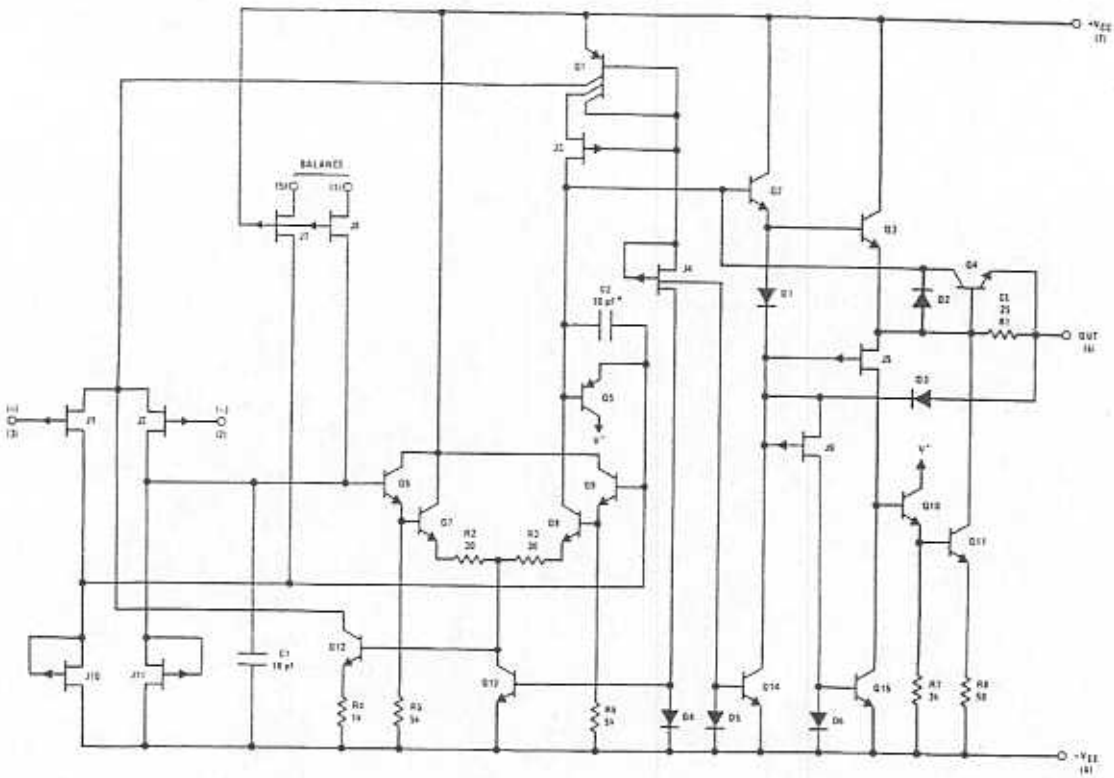
00564665

Equivalent Input Noise Voltage (Expanded Scale)



00564666

Detailed Schematic

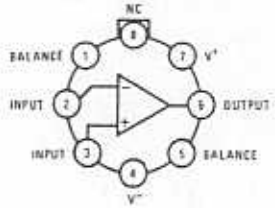


00564613

*C = 3pF in LF357 series.

Connection Diagrams (Top Views)

Metal Can Package (H)

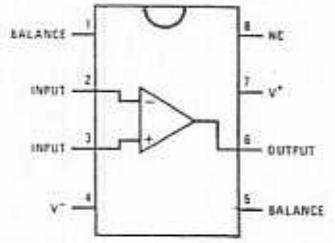


00564614

Order Number LF155H, LF156H, LF256H, LF257H, LF356BH, LF356H, or LF357H
See NS Package Number H08C

*Available per JM38510/11401 or JM38510/11402

Dual-In-Line Package (M and N)



00564629

Order Number LF356M, LF356MX, LF355N, or LF356N
See NS Package Number M08A or N08E

Application Hints

These are op amps with JFET input devices. These JFETs have large reverse breakdown voltages from gate to source and drain eliminating the need for clamps across the inputs. Therefore large differential input voltages can easily be accommodated without a large increase in input current. The maximum differential input voltage is independent of the supply voltages. However, neither of the input voltages should be allowed to exceed the negative supply as this will cause large currents to flow which can result in a destroyed unit.

Exceeding the negative common-mode limit on either input will force the output to a high state, potentially causing a

Application Hints (Continued)

reversal of phase to the output. Exceeding the negative common-mode limit on both inputs will force the amplifier output to a high state. In neither case does a latch occur since raising the input back within the common-mode range again puts the input stage and thus the amplifier in a normal operating mode.

Exceeding the positive common-mode limit on a single input will not change the phase of the output however, if both inputs exceed the limit, the output of the amplifier will be forced to a high state.

These amplifiers will operate with the common-mode input voltage equal to the positive supply. In fact, the common-mode voltage can exceed the positive supply by approximately 100 mV independent of supply voltage and over the full operating temperature range. The positive supply can therefore be used as a reference on an input as, for example, in a supply current monitor and/or limiter.

Precautions should be taken to ensure that the power supply for the integrated circuit never becomes reversed in polarity or that the unit is not inadvertently installed backwards in a socket as an unlimited current surge through the resulting forward diode within the IC could cause fusing of the internal conductors and result in a destroyed unit.

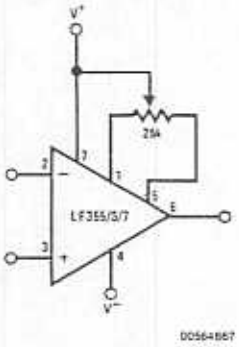
All of the bias currents in these amplifiers are set by FET current sources. The drain currents for the amplifiers are therefore essentially independent of supply voltage.

As with most amplifiers, care should be taken with lead dress, component placement and supply decoupling in order to ensure stability. For example, resistors from the output to an input should be placed with the body close to the input to minimize "pickup" and maximize the frequency of the feedback pole by minimizing the capacitance from the input to ground.

A feedback pole is created when the feedback around any amplifier is resistive. The parallel resistance and capacitance from the input of the device (usually the inverting input) to AC ground set the frequency of the pole. In many instances the frequency of this pole is much greater than the expected 3dB frequency of the closed loop gain and consequently there is negligible effect on stability margin. However, if the feedback pole is less than approximately six times the expected 3 dB frequency a lead capacitor should be placed from the output to the input of the op amp. The value of the added capacitor should be such that the RC time constant of this capacitor and the resistance it parallels is greater than or equal to the original feedback pole time constant.

Typical Circuit Connections

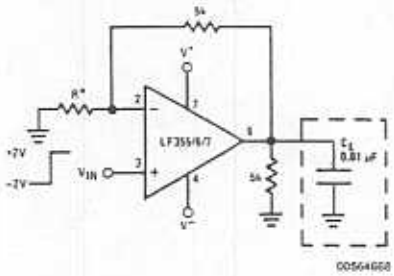
V_{OS} Adjustment



00564667

- V_{OS} is adjusted with a 25k potentiometer
- The potentiometer wiper is connected to V+
- For potentiometers with temperature coefficient of 100 ppm/°C or less the additional drift with adjust is = 0.5µV/°C/mV of adjustment
- Typical overall drift: 5µV/°C ±(0.5µV/°C/mV of adj.)

Driving Capacitive Loads



00564668

* LF155/6 R = 5k

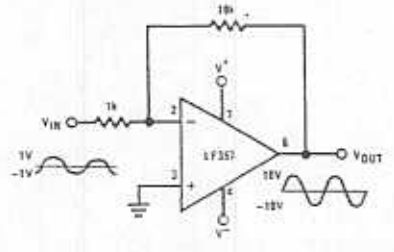
  LF357 R = 1.25k

  Due to a unique output stage design, these amplifiers have the ability to drive large capacitive loads and still maintain stability. $C_{L(MAX)} \approx 0.01\mu F$.

  Overshoot ≤ 20%

  Settling time (t_s) ≈ 5µs

LF357, A Large Power BW Amplifier



00564615

For distortion ≤ 1% and a 20 Vp-p V_{OUT} swing, power bandwidth is: 500kHz.

FAIRCHILD
SEMICONDUCTOR®

1N4001 - 1N4007

Features

- Low forward voltage drop.
- High surge current capability.

DO-41
COLOR BAND DENOTES CATHODE

General Purpose Rectifiers

Absolute Maximum Ratings*

T_A = 25°C unless otherwise noted

Symbol	Parameter	Value							Units
		4001	4002	4003	4004	4005	4006	4007	
V_{RRM}	Peak Repetitive Reverse Voltage	50	100	200	400	600	800	1000	V
$I_{F(AV)}$	Average Rectified Forward Current, .375 " lead length @ T_A = 75°C	1.0							A
I_{FSM}	Non-repetitive Peak Forward Surge Current 8.3 ms Single Half-Sine-Wave	30							A
T_{STG}	Storage Temperature Range	-55 to +175							°C
T_J	Operating Junction Temperature	-55 to +175							°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics

Symbol	Parameter	Value	Units
P_D	Power Dissipation	3.0	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	50	°C/W

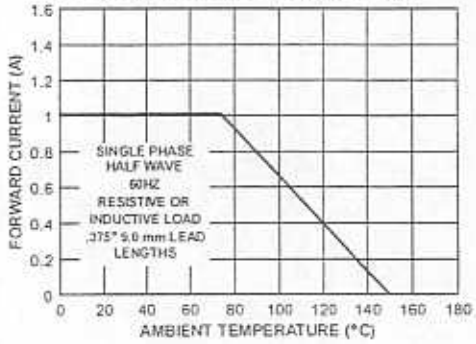
Electrical Characteristics

T_A = 25°C unless otherwise noted

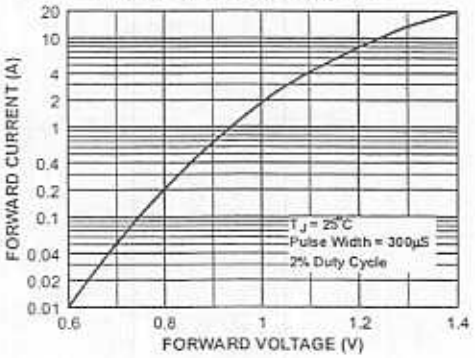
Symbol	Parameter	Device							Units
		4001	4002	4003	4004	4005	4006	4007	
V_F	Forward Voltage @ 1.0 A	1.1							V
I_{rr}	Maximum Full Load Reverse Current, Full Cycle T_A = 75°C	30							µA
I_R	Reverse Current @ rated V_R T_A = 25°C T_A = 100°C	5.0 500							µA µA
C_T	Total Capacitance V_R = 4.0 V, f = 1.0 MHz	15							pF

Typical Characteristics

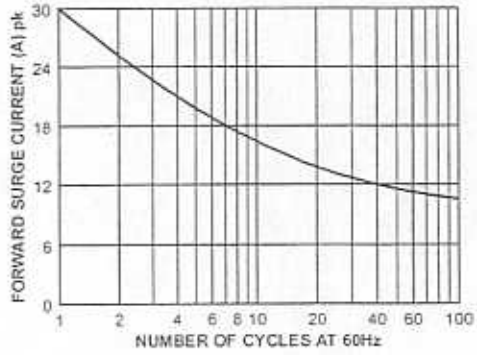
Forward Current Derating Curve



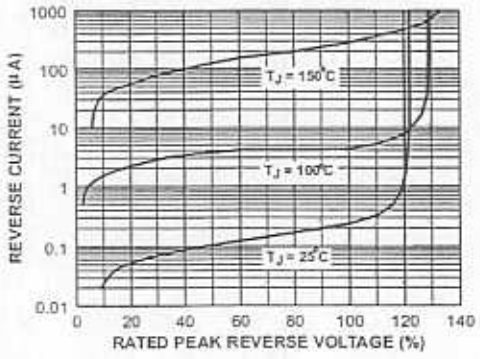
Forward Characteristics



Non-Repetitive Surge Current



Reverse Characteristics



FAIRCHILD
SEMICONDUCTOR®

1N/FDLL 914/A/B / 916/A/B / 4148 / 4448

DO-35

LL-34

THE PLACEMENT OF THE EXPANSION GAP HAS NO RELATIONSHIP TO THE LOCATION OF THE CATHODE TERMINAL

COLOR BAND MARKING

DEVICE	1ST BAND	2ND BAND
FDLL914	BLACK	BROWN
FDLL914A	BLACK	GRAY
FDLL914B	BROWN	BLACK
FDLL916	BLACK	RED
FDLL916A	BLACK	WHITE
FDLL916B	BROWN	BROWN
FDLL4148	BLACK	BROWN
FDLL4448	BROWN	BLACK

Small Signal Diode

Absolute Maximum Ratings*

T_A = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{RRM}	Maximum Repetitive Reverse Voltage	100	V
$I_{F(AV)}$	Average Rectified Forward Current	200	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond	 1.0 4.0	 A A
T_{stg}	Storage Temperature Range	-65 to +200	°C
T_J	Operating Junction Temperature	175	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These ratings are based on a maximum junction temperature of 200 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

Symbol	Characteristic	Max	Units
		1N/FDLL 914/A/B / 4148 / 4448	
P_D	Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	300	°C/W